[CLAIMS]

[Claim 1]

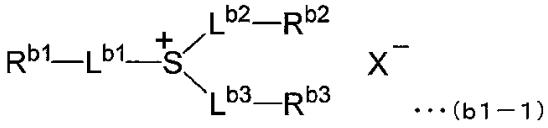
A method of forming a resist pattern, comprising:

a step (i) of forming a resist film having a film thickness of 7 μm or more on a support using a resist composition;

a step (ii) of exposing the resist film to light; and

a step (iii) of developing the exposed resist film to form a resist pattern,

wherein the resist composition contains a base material component (A) whose solubility in a developing solution is changed due to an action of an acid, and an acid generator (B1) formed of a compound represented by General Formula (b1-1):



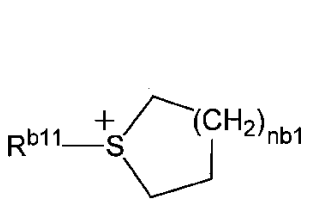
wherein R^{b1} represents an aryl group which may have a substituent, R^{b2} and R^{b3} each independently represent an aliphatic hydrocarbon group, R^{b2} and R^{b3} may be bonded to each other to form a ring structure, L^{b1}, L^{b2}, and L^{b3} each independently represent a divalent linking group or a single bond, and X^- represents a counter anion.

[Claim 2]

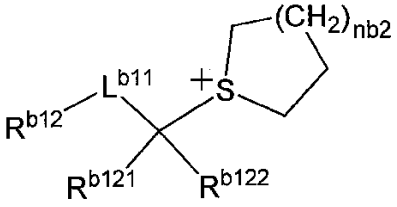
The method of forming a resist pattern according to Claim 1, wherein L^{b1} in Formula (b1-1) is a single bond.

[Claim 3]

The method of forming a resist pattern according to Claim 1, wherein the cation moiety of the acid generator (B1) a cation represented by General Formula (ca-1-01) or a cation represented by General Formula (ca-1-02):



(ca−1−01)



(ca−1−02)

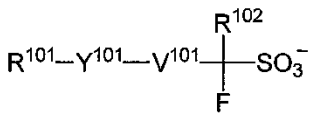
wherein Ra^{b11} and Ra^{b12} each independently represent an aryl group which may have a substituent, L^{b11} represents -C(=O)- or -C(=O)-O-, R^{b121} and R^{b122} each independently represent a hydrogen atom or an alkyl group having 1 to 5 carbon atoms, nb1 represents an integer of 1 to 3, and nb2 represents an integer of 1 to 3.

[Claim 4]

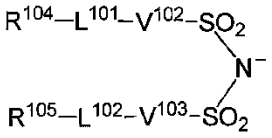
The method of forming a resist pattern according to Claim 3, wherein the cation moiety of the acid generator (B1) a cation represented by General Formula (ca-1-01).

[Claim 5]

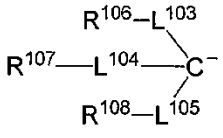
The method of forming a resist pattern according to any one of Claims 1 to 4, wherein X^- in Formula (b1-1) is an anion represented by General Formula (b1-1-an1), an anion represented by General Formula (b1-1-an2), or an anion represented by General Formula (b1-1-an3),



(b1−1−an1)



(b1−1−an2)



(b1−1−an3)

wherein R^{101} and R^{104} to R^{108} each independently represent a cyclic group which may have a substituent, a chain alkyl group which may have a substituent, or a chain alkenyl group which may have a substituent, R^{104} and R^{105} may be bonded to each other to form a ring structure, R^{102} represents a fluorinated alkyl group having 1 to 5 carbon atoms, or a fluorine atom, Y^{101} represents a divalent linking group containing an oxygen atom, or

a single bond, V^{101} to V^{103} each independently represent a single bond, an alkylene group, or a fluorinated alkylene group, L^{101} and L^{102} each independently represent a single bond or an oxygen atom, and L^{103} to L^{105} each independently represent a single bond, -CO-, or $-SO_2-$.

[Claim 6]

The method of forming a resist pattern according to any one of Claims 1 to 5, wherein in the step (ii), the resist film is irradiated with KrF excimer laser light.